



10Amp. Schottky Barrier Rectifiers MBR10200J3

$I_{F(AV)}$	2 × 5A
V_{RRM}	200V
T_j	175°C
$V_{F(TYP.)}$	0.7V

Features

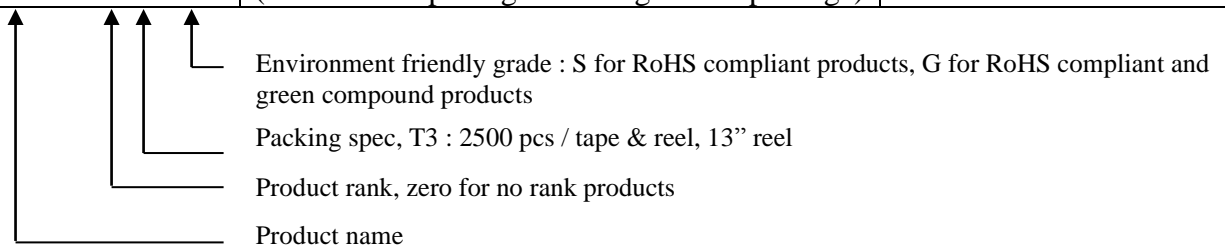
- 175°C operating junction temperature
- Low V_F and low I_R type
- Metal silicon junction, major carrier conduction
- 10A total (5A per diode leg)
- Guardring for over voltage protection
- Low power loss, high efficiency
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection application
- Pb-free lead plating and halogen-free package

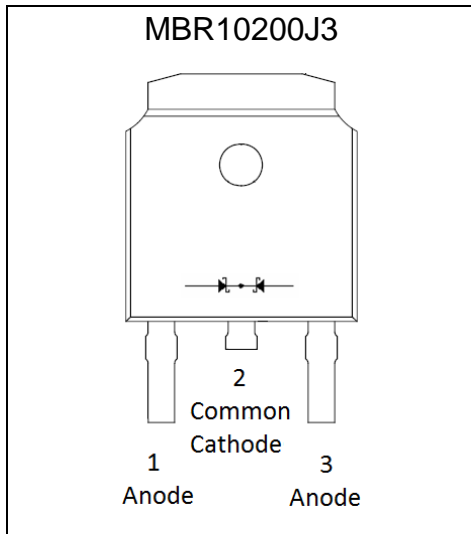
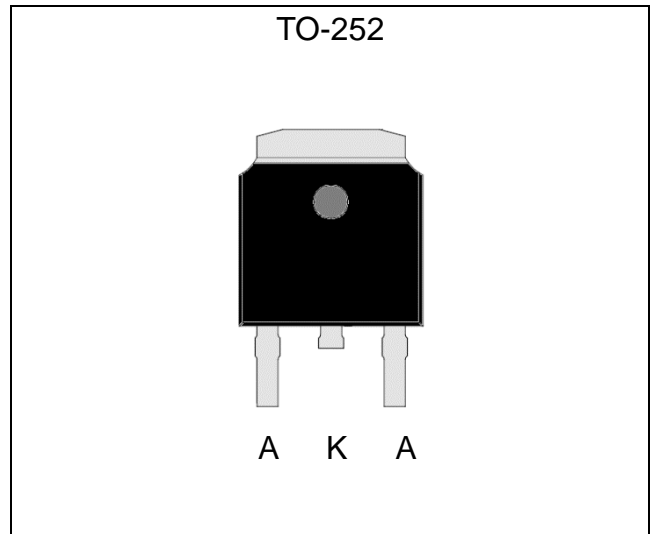
Mechanical Data

- Case: TO-252 molded plastic
- Mounting Position: Any
- Weight: 0.34 grams approximately
- Terminals: Pure tin plated, lead-free, solderable per MIL-STD-750 method 2026
- Epoxy: UL 94V-0 rate flame retardant
- Polarity : Indicated by diode symbol

Ordering Information

Device	Package	Shipping
MBR10200J3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Equivalent Circuit

Outline

Maximum Ratings and Electrical Characteristics (Per Diode Leg)

(Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.)

Parameter	Symbol	Value	Units
Maximum Recurrent peak reverse voltage	V_{RRM}	200	V
Maximum RMS voltage	V_{RMS}	140	V
Maximum DC blocking voltage	V_{DC}	200	V
Maximum instantaneous forward voltage at (Note 1)	V_F	$I_F=5A, T_C=25^\circ C$	0.90
		$I_F=5A, T_C=125^\circ C$	0.74
		$I_F=10A, T_C=25^\circ C$	1.00
		$I_F=10A, T_C=125^\circ C$	0.87
Maximum Average forward rectified current @ $T_C=133^\circ C$	Per Diode	5	A
	Per Device	10	
Peak repetitive forward current (square wave, 20kHz, $T_C=133^\circ C$)	I_{FRM}	10	A
Non-repetitive peak forward surge current @ 8.3ms single half sine wave superimposed on rated load (JEDEC method)	I_{FSM}	110	A
Peak repetitive reverse surge current (Note 1), $T_J < 175^\circ C$	I_{RRM}	2	A
Maximum instantaneous reverse current at	I_R	$V_R=200V, T_C=25^\circ C$	5 μA
		$V_R=200V, T_C=125^\circ C$	5 mA
Voltage rate of change, (rated V_R)	dV/dt	10,000	V/ μs
Typical junction capacitance @ $f=1MHz$ and applied 5V reverse voltage	C_J	65 (typ.)	pF
ESD susceptibility (Note 2)		8000	V
Storage temperature range	T_{stg}	-65 ~ +175	$^\circ C$
Operating junction temperature range	T_J	-65 ~ +175	$^\circ C$

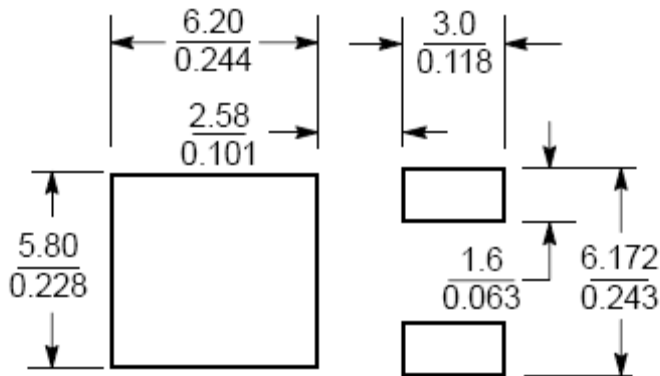
Notes : 1. 2.0 μs pulse width, $f=1.0kHz$

2. Human body model, 1.5k Ω in series with 100pF

Thermal Data

Parameter		Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-case	Per diode	R _{th,j-c}	2.4	°C/W
	Total		4	
Maximum Thermal Resistance, Junction-to-ambient		R _{th,j-a}	90	°C/W

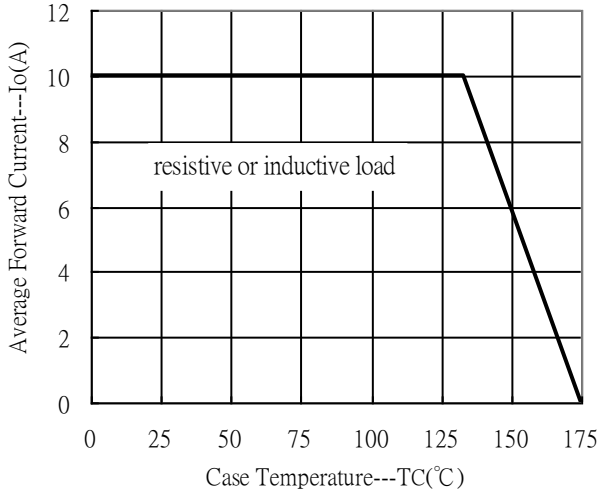
Recommended soldering footprint



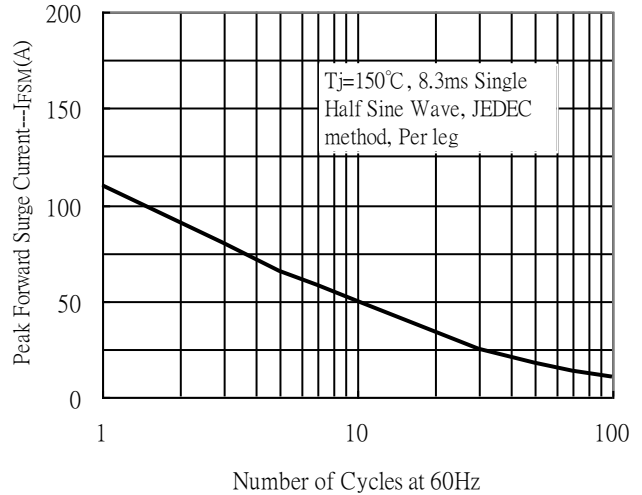
Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

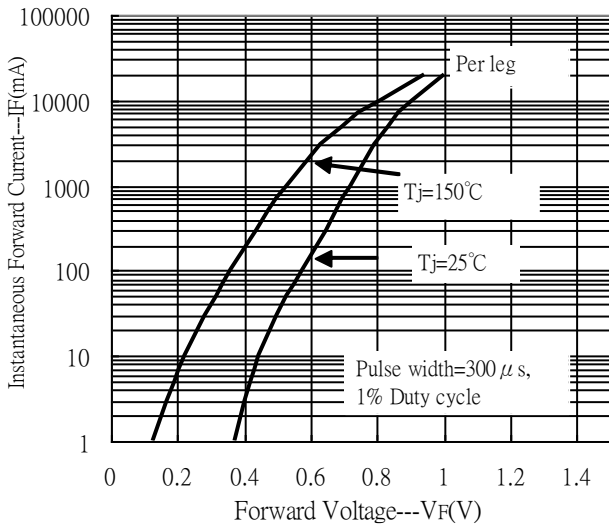
Forward Current Derating Curve



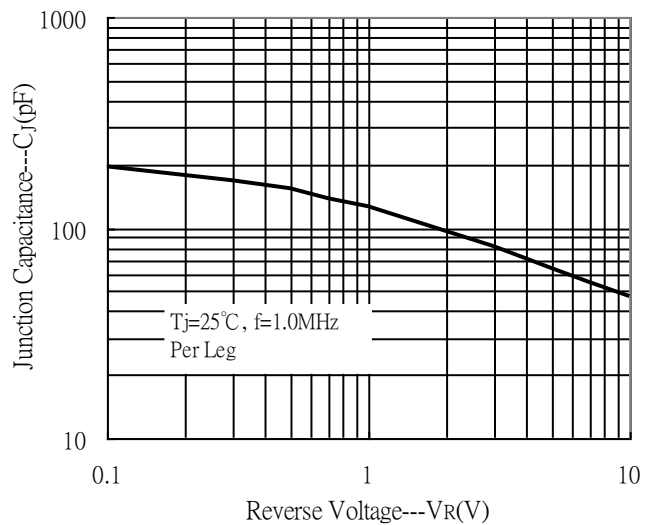
Maximum Non-Repetitive Forward Surge Current



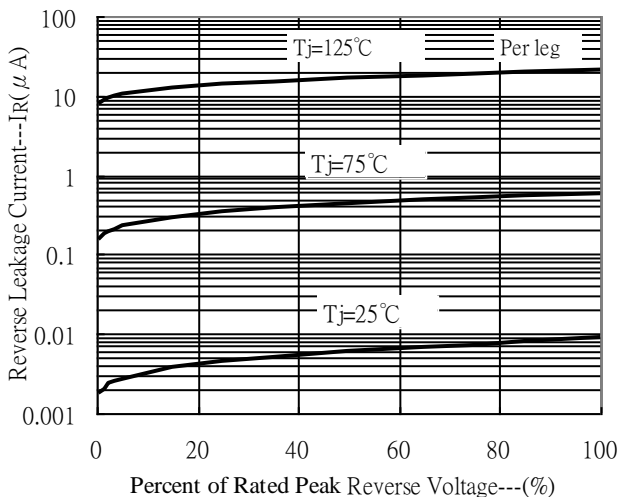
Forward Current vs Forward Voltage



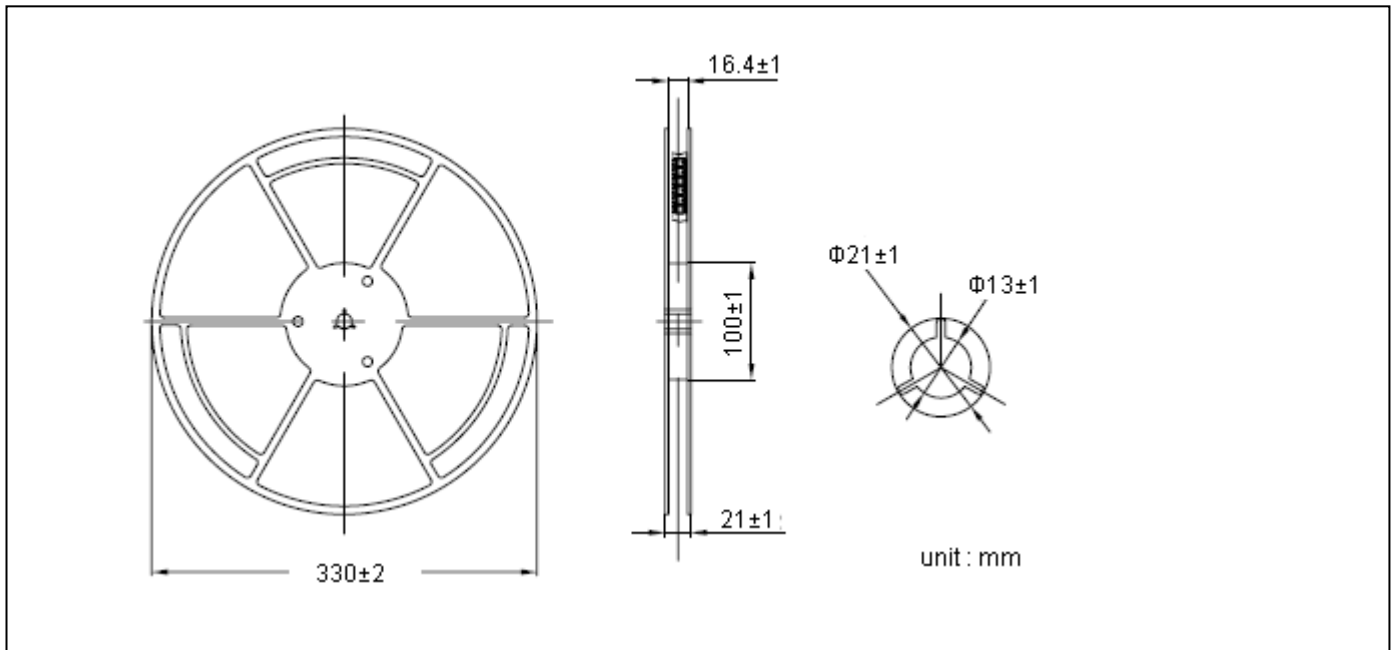
Junction Capacitance vs Reverse Voltage



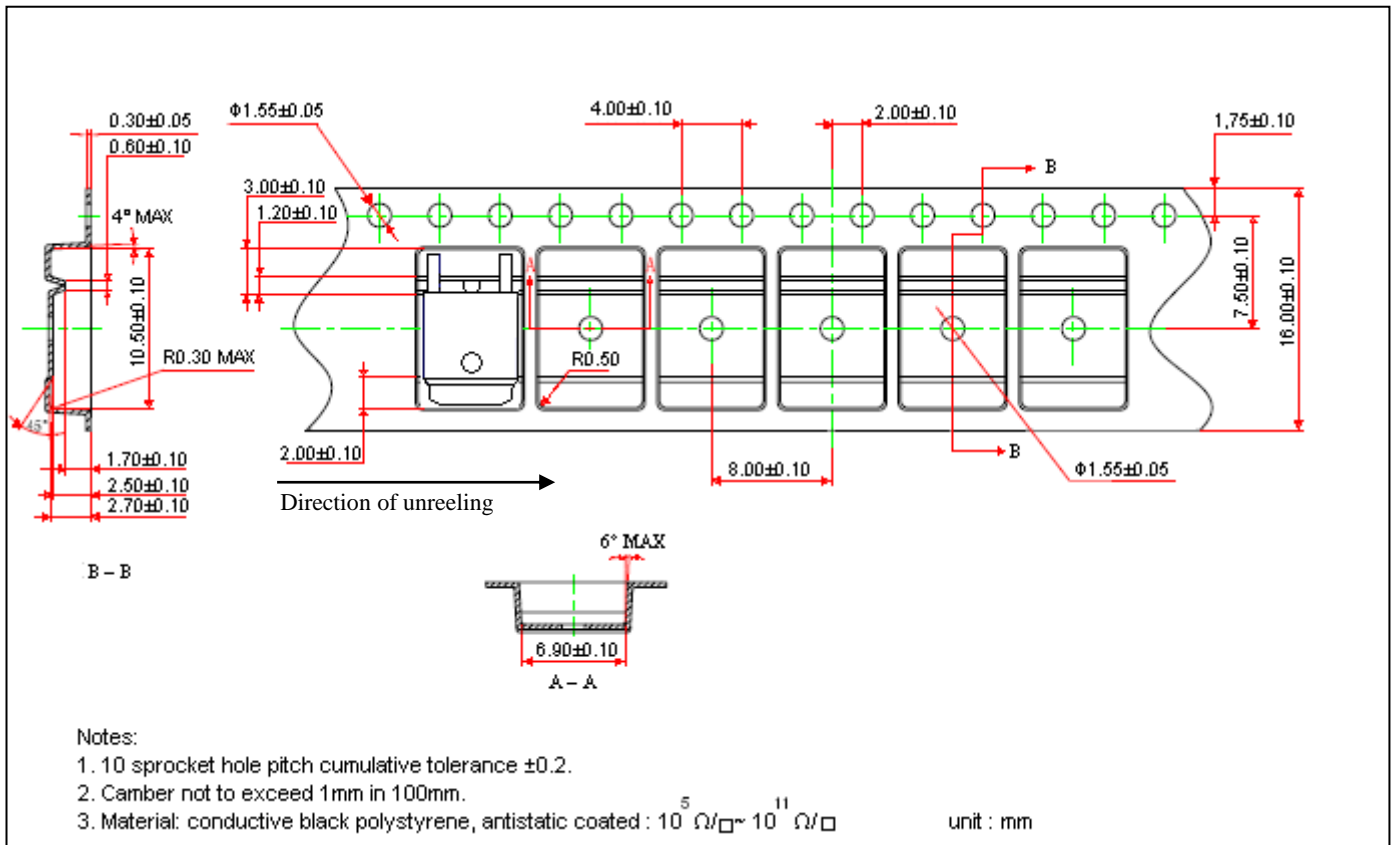
Reverse Leakage Current vs Reverse Voltage



Reel Dimension



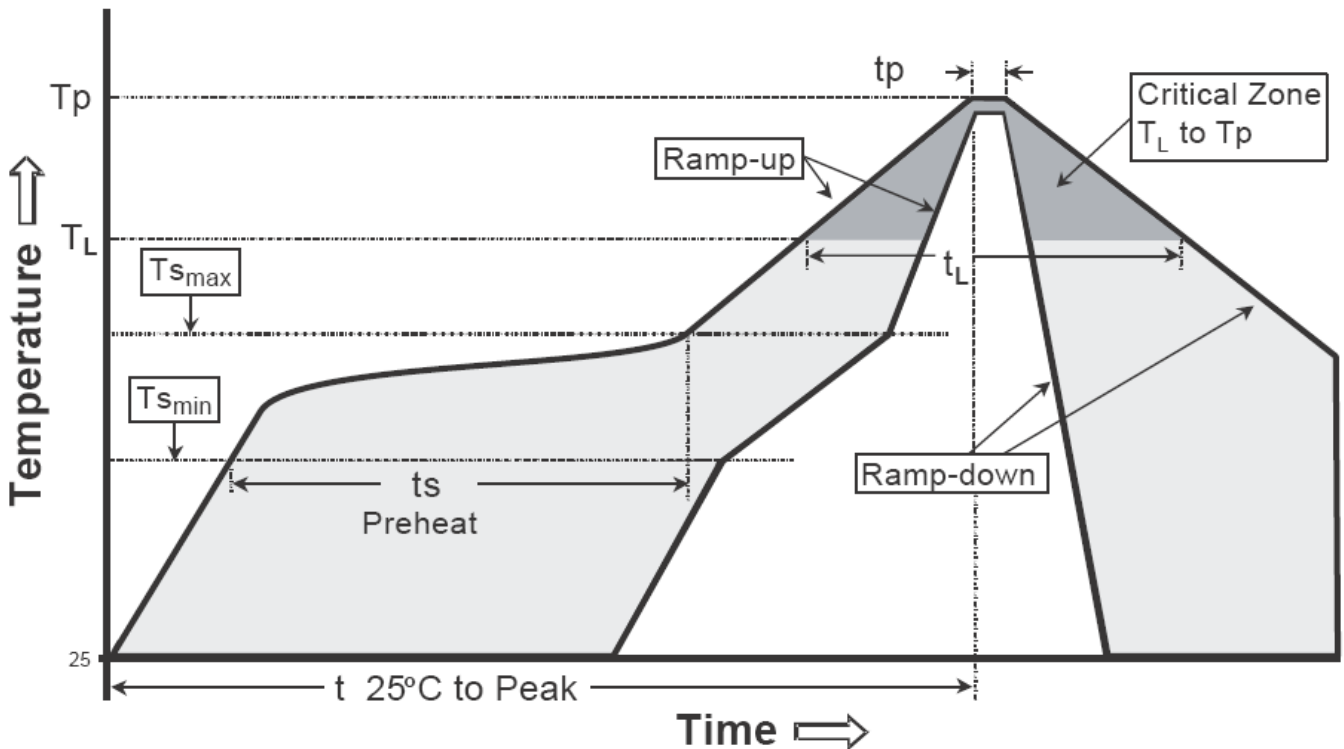
Carrier Tape Dimension



Recommended wave soldering condition

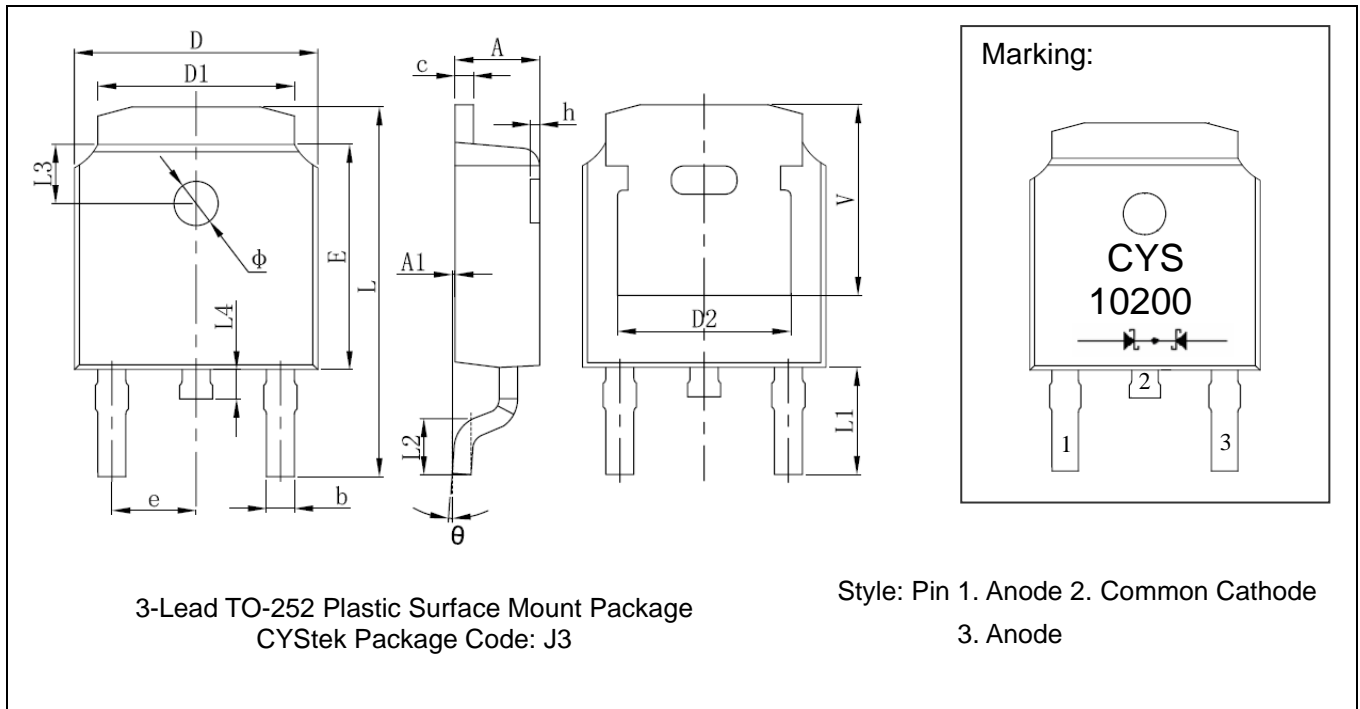
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

TO-252 Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	L	0.382	0.406	9.712	10.312
A1	0.000	0.005	0.000	0.127	L1	0.114	REF	2.900	REF
b	0.025	0.030	0.635	0.770	L2	0.055	0.067	1.400	1.700
c	0.018	0.023	0.460	0.580	L3	0.063	REF	1.600	REF
D	0.256	0.264	6.500	6.700	L4	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	Φ	0.043	0.051	1.100	1.300
D2	0.190	REF	4.830	REF	θ	0°	8°	0°	8°
E	0.236	0.244	6.000	6.200	h	0.000	0.012	0.000	0.300
e	0.086	0.094	2.186	2.386	v	0.207	REF	5.250	REF

- Notes:**
- Controlling dimension: millimeters.
 - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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